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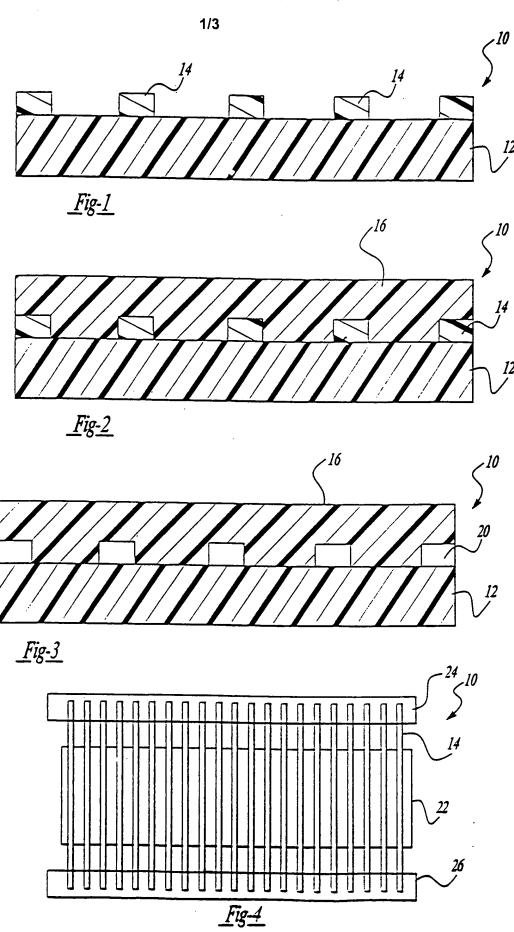
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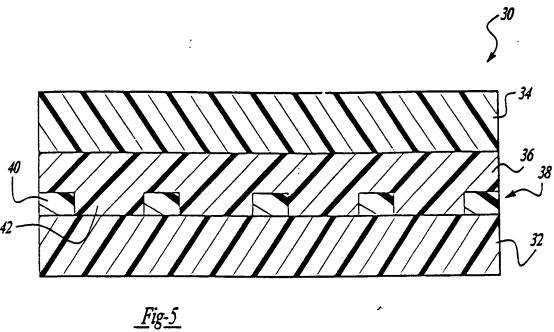
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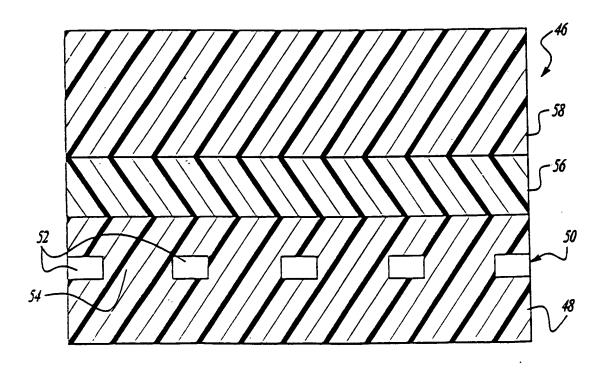
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GRATING USING A SACRIFICIAL LAYER
Inventor(s): Michael P. Nesnidal et al.
Attorney Docket No. NGC-00087DA (11-0983D)

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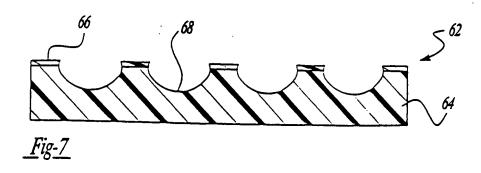


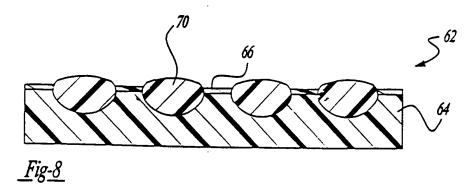


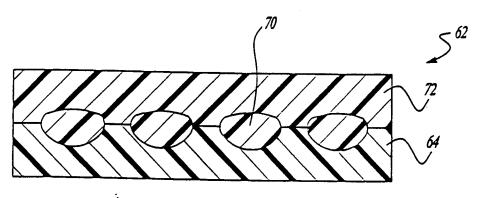
<u>Fig-6</u>

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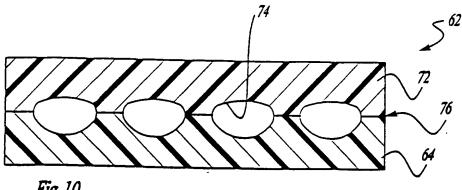
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<u>Fig-9</u>



<u>Fig-10</u>